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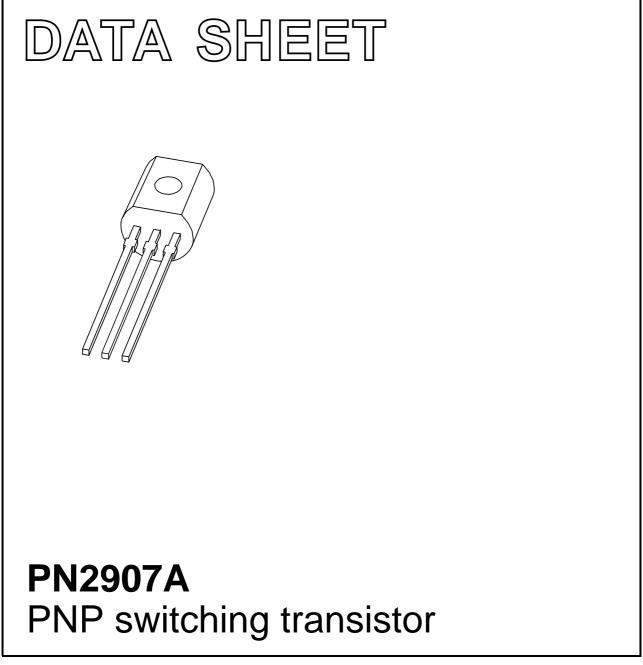
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DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 May 05 2004 Oct 11



FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

• Switching and linear amplification.

DESCRIPTION

PNP switching transistor in a TO-92; SOT54 plastic package. NPN complement: PN2222A.

PINNING

PIN	DESCRIPTION	
1	collector	
2	base	
3	emitter	

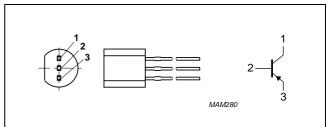


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-60	V
V _{CEO}	collector-emitter voltage	open base	-	-60	V
I _C	collector current (DC)		-	-600	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	500	mW
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V}; I_{C} = -150 \text{ mA}$	100	300	
f _T	transition frequency	$V_{CE} = -20 \text{ V}; I_{C} = -50 \text{ mA}; f = 100 \text{ MHz}$	200	-	MHz
t _{off}	turn-off time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA}; I_{Boff} = 15 \text{ mA}$	-	365	ns

ORDERING INFORMATION

TYPE NUMBER		PACKAGE		
TIFE NOMBER	NAME DESCRIPTION VI			
PN2907A	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54	

PN2907A

PN2907A

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-60	V
V _{CEO}	collector-emitter voltage	open base	-	-60	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-600	mA
I _{CM}	peak collector current		-	-800	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

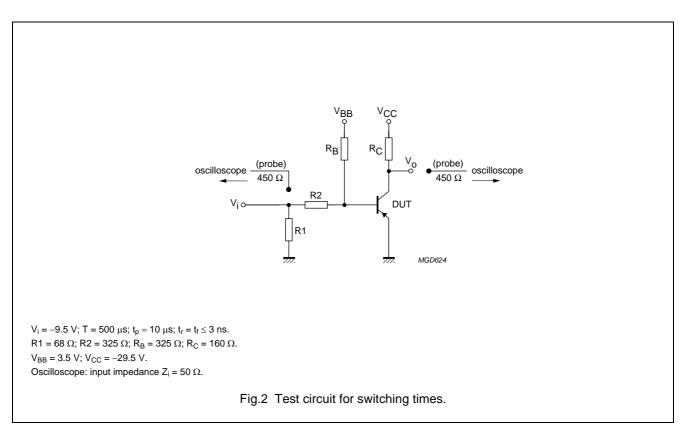
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

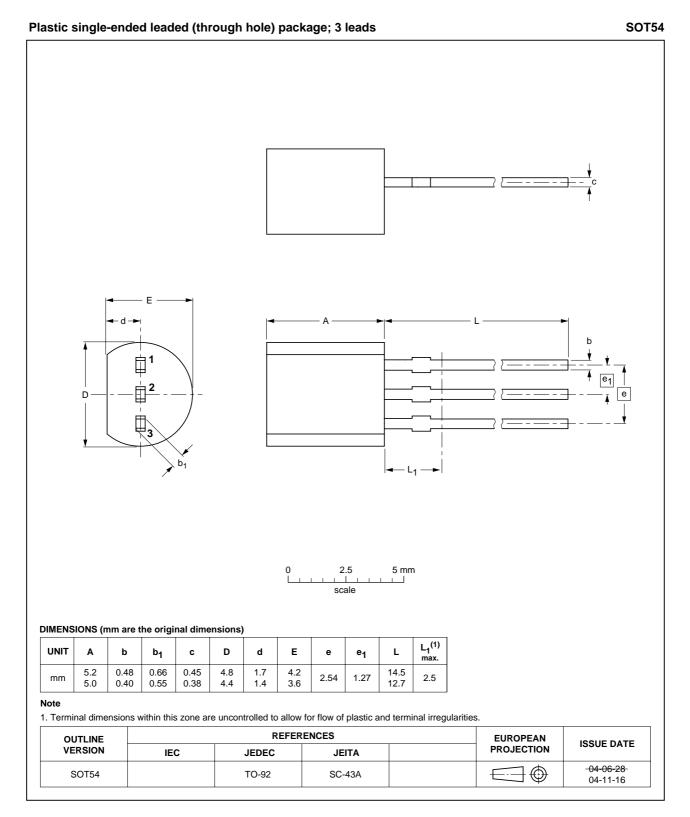
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-10	nA
		$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 125 \text{ °C}$	-	-10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$	-	-50	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V}; I_{C} = -0.1 \text{ mA}$	75	_	
		$V_{CE} = -10 \text{ V}; I_C = -1 \text{ mA}$	100	_	
		$V_{CE} = -10 \text{ V}; I_{C} = -10 \text{ mA}$	100	-	
		$V_{CE} = -10 \text{ V}; I_{C} = -150 \text{ mA}$	100	300	
		$V_{CE} = -10 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	50	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = –150 mA; I _B = –15 mA	-	-400	mV
		$I_{C} = -500 \text{ mA}; I_{B} = -50 \text{ mA}$	-	-1.6	V
V _{BEsat}	base-emitter saturation voltage	$I_{C} = -150 \text{ mA}; I_{B} = -15 \text{ mA}$	-	-1.3	V
		I _C = –150 mA; I _B = –50 mA	-	-2.6	V
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	8	pF
Ce	emitter capacitance	$V_{EB} = -2 \text{ V}; I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	-	30	pF
f _T	transition frequency	$V_{CE} = -20 \text{ V}; \text{ I}_{C} = -50 \text{ mA}; \text{ f} = 100 \text{ MHz}$	200	-	MHz

PN2907A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Switching	Switching times (between 10 % and 90 % levels); see Fig.2					
t _{on}	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$	_	40	ns	
t _d	delay time	I _{Boff} = 15 mA	-	12	ns	
t _r	rise time		-	30	ns	
t _{off}	turn-off time		-	365	ns	
t _s	storage time		_	300	ns	
t _f	fall time		_	65	ns	



PACKAGE OUTLINE



PN2907A

PN2907A

DATA SHEET STATUS	
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DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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